## Silicon N-Channel MOS FET

# **HITACHI**

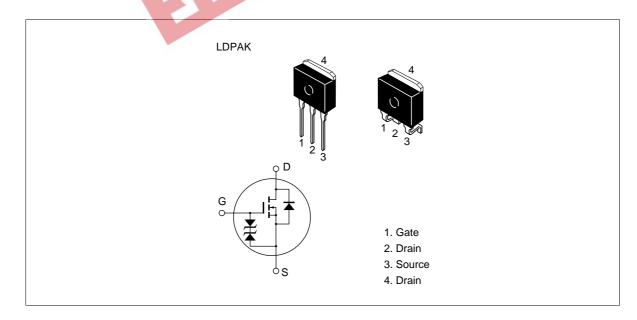
## **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- T. Com. cn Suitable for switching regulator and DC-DC converter

### **Outline**





## **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{ t DSS}$	600	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub>	3	А
Drain peak current	l *1 D(pulse)	6	A
Body to drain diode reverse drain current	I <sub>DR</sub>	3	Α
Channel dissipation	Pch*2	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at  $T_c = 25^{\circ}C$ 

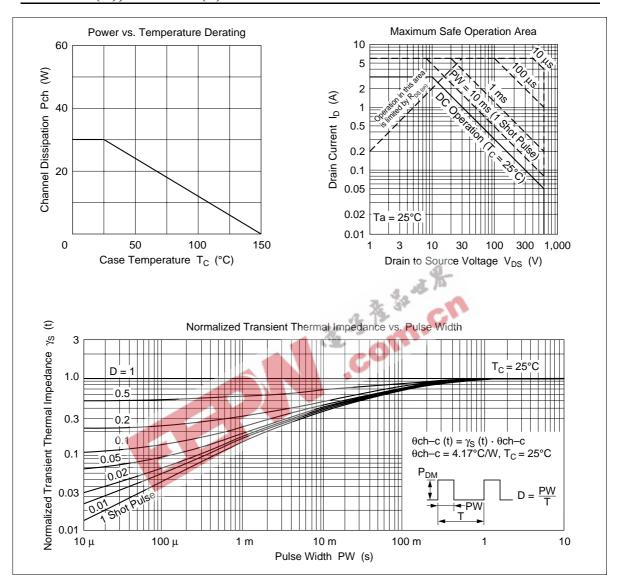


## **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	250	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	R <sub>DS(on)</sub>	_	3.8	5.0	Ω	$I_D = 1 \text{ A, V}_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	1.2	2.0	_	S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	295	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	70	- 35	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	12	少了	pF	
Turn-on delay time	$t_{d(on)}$	-	8	-0	ns	$I_D = 1 A, V_{GS} = 10 V,$
Rise time	t <sub>r</sub>	<b>-</b> ••	25	-	ns	$R_L = 30 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	1/1	65	_	ns	_
Fall time	t <sub>f</sub>	77	30	_	ns	_
Body to drain diode forward voltage	V <sub>DF</sub>	_	0.9	_	V	$I_F = 2 A, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	_	220	_	ns	$I_F = 2 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

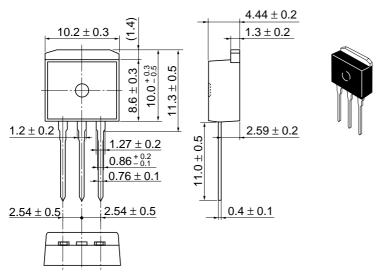
Note 1. Pulse test

See characteristic curves of 2SK1572.





Unit: mm



Lita ahi Ca da	LDDAK (L)
Hitachi Code	LDPAK (L)
JEDEC	<del>_</del>
EIAJ	_
Weight (reference value)	1.4 a

#### **Cautions**

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